

In the Claims:

1.-27. (Canceled)

28. (Previously Presented) A conductive structure comprising:

a first conductor;

a plurality of atomic layers of a second conductor directly on the first conductor; and

a first solid material directly on the plurality of atomic layers of the second conductor, remote from the first conductor, the first material being penetrable by the plurality of atomic layers of the second conductor relative to at least a second material other than the second conductor.

29. (Original) A structure according to Claim 28 wherein the first conductor comprises a platinum group metal, the first material comprises a halogen, the second conductor comprises a metal and the second material comprises oxygen.

30. (Original) A structure according to Claim 28 further comprising a substrate on the first conductor, remote from the plurality of atomic layers of the second conductor.

31. (Original) A structure according to Claim 30 wherein the substrate comprises an integrated circuit wafer.

32. (Original) A structure according to Claim 28 wherein the first material comprises about a monolayer of the first material.

33. (Original) A conductive structure comprising:

a first layer comprising ruthenium;

a second layer comprising a plurality of atomic layers of copper directly on the first layer comprising ruthenium; and

a third layer comprising iodine directly on the second layer comprising a plurality of atomic layers of copper, remote from the first layer comprising ruthenium.

34. (Original) A structure according to Claim 33 wherein the third layer comprises about one monolayer of iodine.

35. (Original) A structure according to Claim 33 further comprising a substrate on the first layer, remote from the second layer .

36. (Original) A structure according to Claim 35 wherein the substrate comprises an integrated circuit wafer.